



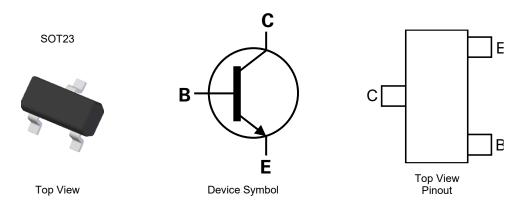
### **40V NPN SMALL-SIGNAL TRANSISTOR IN SOT23**

### **Features**

- Epitaxial Planar Die Construction
- Low Saturation Voltage V<sub>CE(sat)</sub> < 300mV @ 150mA</li>
- Complementary PNP Type: MMBT2907A
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under a separate datasheet (MMBT2222AQ)

### **Mechanical Data**

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



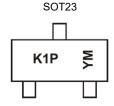
## Ordering Information (Note 4)

Orderable Part Number	Dookaga	Marking	Reel Size (inches)	Tape Width (mm)	Pac	king	
Orderable Part Number	Package	Marking	Reel Size (Illiches)	rape width (min)	Qty.	Carrier	
MMBT2222A-7-F	SOT23	K1P	7	8	3,000	Reel	
MMBT2222A-13-F	SOT23	K1P	13	8	10,000	Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## Marking Information



K1P = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  or  $\underline{Y}$  = Year (ex: M = 2025) M or  $\overline{M}$  = Month (ex: 9 = September)

#### Date Code Key

Year	2002	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	N	-	М	N	Р	R	S	Т	U	V	W	Х
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## Absolute Maximum Ratings (@ TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	75	V
Collector-Emitter Voltage	VCEO	40	V
Emitter-Base Voltage	VEBO	6.0	V
Collector Current	Ic	600	mA
Peak Pulse Collector Current (Single Pulse)	Ісм	800	mA
Peak Pulse Base Current	Івм	200	mA

## Thermal Characteristics (@ TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Collector Dower Discinction	(Note 5)	D-	310	mW	
Collector Power Dissipation	(Note 6)	P <sub>D</sub>	350		
Thermal Decistance, Junction to Ambient	(Note 5)	D	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	357		
Thermal Resistance, Junction to Leads (Note 7)		R <sub>0JL</sub>	350	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

# ESD Ratings (Note 8)

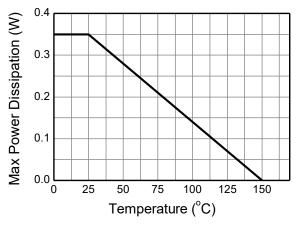
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady state.
- 6. Same as Note 5, except the device is mounted on 15mm x 15mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the leads). 8. Refer to JEDEC specifications JESD22-A114 and JESD22-A115.



# **Thermal Characteristics and Derating Information**



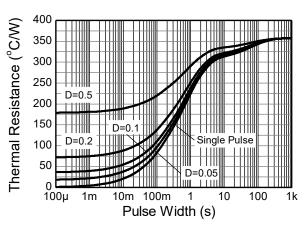


Figure 1. Derating Curve

Figure 2. Transient Thermal Impedance

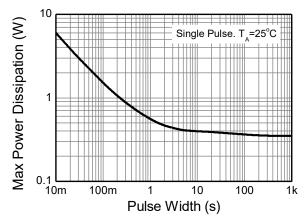


Figure 3. Pulse Power Dissipation



# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	ВУсво	75	_	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 9)	BVceo	40	_	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BVEBO	6.0	_	V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0
Collector Cutoff Current	lana	_	10	nA	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0
Collector Cutoff Current	I <sub>CBO</sub>	_	10	μA	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0, T <sub>A</sub> = +150°C
Collector Cutoff Current	ICEX	_	10	nA	V <sub>CE</sub> = 60V, V <sub>EB(off)</sub> = 3.0V
Collector Cutoff Current	I <sub>CEV</sub>		10	nA	$V_{CE} = 60V, V_{BE} = \pm 0.25V$
Emitter Cutoff Current	I <sub>EBO</sub>	_	10	nA	$V_{EB} = 5.0V, I_C = 0$
Base Cutoff Current	I <sub>BL</sub>	_	20	nA	V <sub>CE</sub> = 60V, V <sub>EB(off)</sub> = 3.0V
ON CHARACTERISTICS (Note 9)			•	•	` '
		35 50 75	_		Ic = 100μA, VcE = 10V Ic = 1.0mA, VcE = 10V Ic = 10mA, VcE = 10V
DC Current Gain	hfE	100 40 50 35	300 — — —	Ic = 150mA, VcE = 10V Ic = 500mA, VcE = 10V Ic = 10mA, VcE = 10V, T <sub>A</sub> = -55°C Ic = 150mA, VcE = 1.0V	
Collector-Emitter Saturation Voltage	VCE(sat)	_	0.3 1.0	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.6	1.2 2.0	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>obo</sub>	_	8	pF	V <sub>CB</sub> = 10V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	Cibo	_	25	pF	V <sub>EB</sub> = 0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Transition Frequency	f⊤	300	_	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 20mA f = 100MHz
Noise Figure	NF	_	4.0	dB	$V_{CE}$ = 10V, I <sub>C</sub> = 100μA R <sub>S</sub> = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	td	1	10	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA V <sub>BE(off)</sub> = - 0.5V, I <sub>B1</sub> = 15mA
Rise Time	tr		25	ns	$V_{CC} = 30V$ , $I_{C} = 150mA$ , $I_{B1} = 15mA$ $V_{BE(off)} = 0.5V$
Storage Time	t <sub>s</sub>		225	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA I <sub>B1</sub> = -I <sub>B2</sub> = 15mA
Fall Time	t <sub>f</sub>		60	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA, I <sub>B1</sub> = -I <sub>B2</sub> = 15mA

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



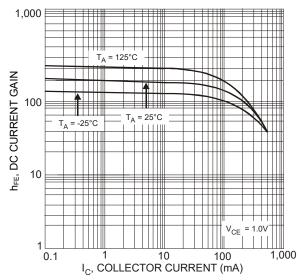


Figure 4. hFE vs. Ic

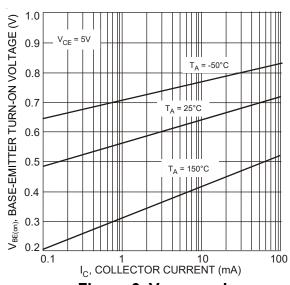


Figure 6. VBE(on) vs. Ic

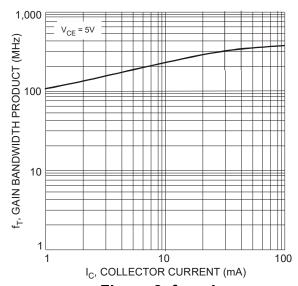


Figure 8. ft vs. lc

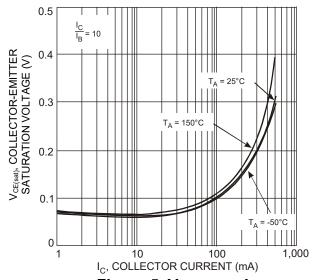


Figure 5.  $V_{\text{CE(sat)}}$  vs.  $I_{\text{C}}$ 

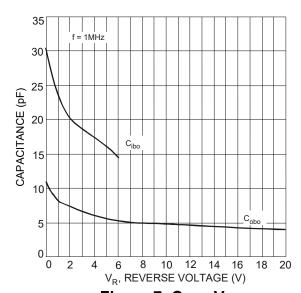


Figure 7. C vs. V<sub>R</sub>

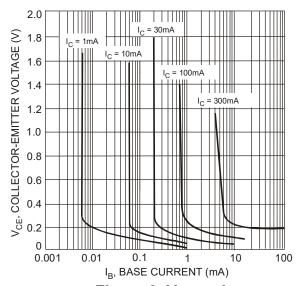


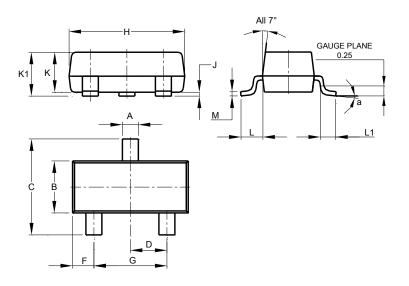
Figure 9. VcE vs. IB



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

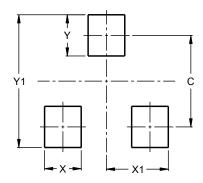


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Ι	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
١	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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